NGTG12N60TF1G

N-Channel IGBT 600V, 12A, VCE(sat);1.4V TO-3PF-3L

ON Semiconductor®

http://onsemi.com



TO-3PF-3L

Features

- V_{CE}(sat)=1.4V typ. (I_C=12A, V_{GE}=15V)
- Low switching loss in higher frequency applications
- Enhansment type
- 5µs short circuit capability
- Adoption of full isolation type package

Applications

- Power factor correction of white goods appliance
- General purpose inverter

Specifications

Absolute Maximum Ratings at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions		Ratings	Unit
Collector to Emitter Voltage	VCES			600	V
Gate to Emitter Voltage	VGES			±20	V
Collector Current (DC)	1	Limited by Tjmax	@ Tc=25°C * ²	24	Α
	IC*1		@ Tc=100°C *2	12	Α
Collector Current (Pulse)	ICP	Pulse width Limited by Tjmax(Ref:ASO graph)		88	Α
Allowable Power Dissipation	PD	Tc=25°C (Our ideal heat dissipation condition) *2		54	W
Junction Temperature	Tj			150	°C
Storage Temperature	Tstg			- 55 to +150	°C

Note: *1 Collector Current is calculated from the following formula.

 $I_{C}(T_{c}) = \frac{3}{R_{th}(j-c) \times V_{CE}(sat) max.(Tjmax, I_{C}(T_{c}))}$

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics at Ta = 25°C, Unless otherwise specified

B	0	0	O Pitt		Ratings		
Parameter	Symbol	Conditions		min	typ	max	Unit
Collector to Emitter Breakdown Voltage	V(BR)CES	I _C =500μA, V _{GE} =0V		600			V
Collector to Emitter Cut off Current		V _{CE} =600V, V _{GE} =0V T _{c=25°C} T _{c=125°C}	Tc=25°C			10	μΑ
	ICES				1	mA	
Gate to Emitter Leakage Current	IGES	V _{GE} =±20V, V _{CE} =0V				±100	nA
Gate to Emitter Threshold Voltage	V _{GE} (th)	V _{CE} =20V, I _C =250μA		4.5		6.5	V
Collector to Emitter Saturation Voltage	\/o= (.)	V _{GF} =15V, I _C =12A	Tc=25°C		1.4	1.6	V
	VCE (sat)	VGE=15V, IC=12A	Tc=125°C		1.6		V
Input Capacitance	Cies			2000		pF	
Output Capacitance	Coes	V _{CE} =20V,f=1MHz			60		pF
Reverse Transfer Capacitance	Cres			50		pF	

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

^{*2} Our condition is radiation from backside.

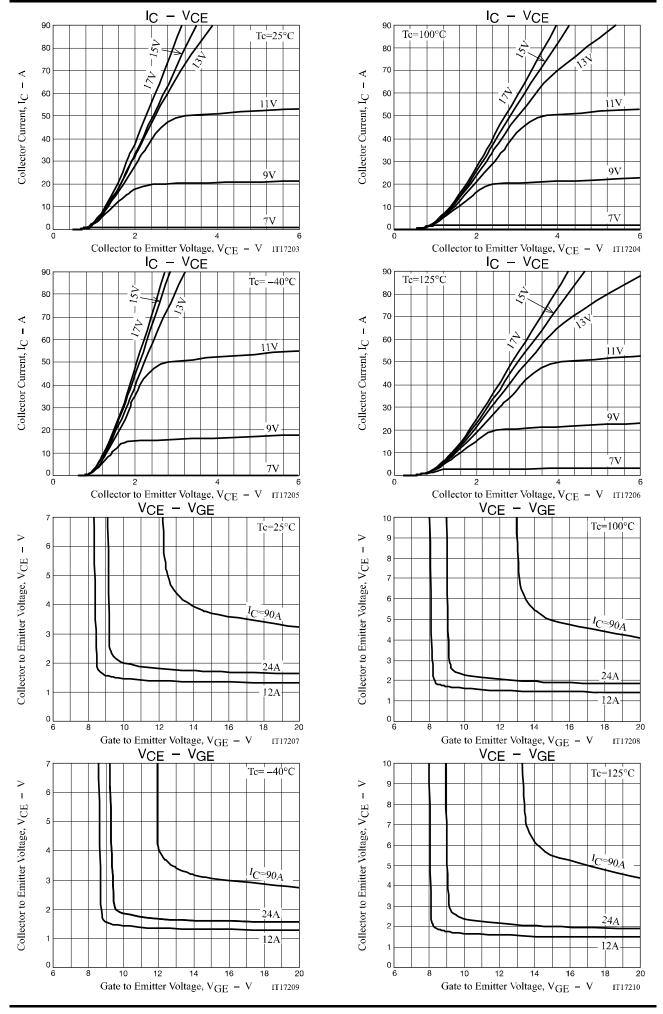
NGTG12N60TF1G

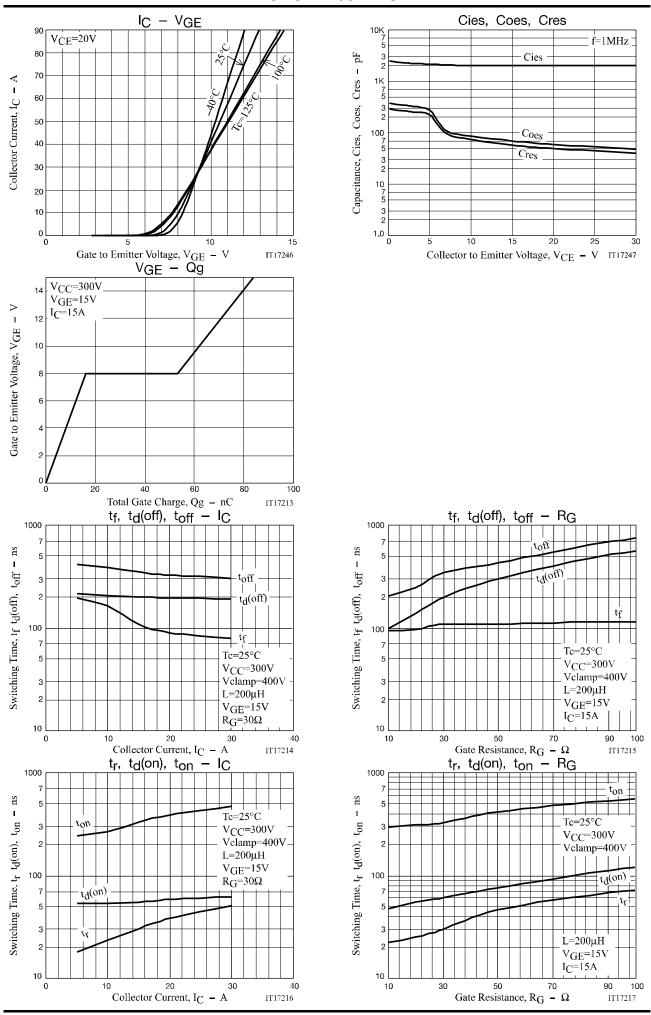
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Parameter	0	Conditions	Ratings	11.2		
	Symbol	Conditions	min	typ	max	Unit
Turn-ON Delay Time	t _d (on)	V _{CC} =300V,I _C =15A R _G =30Ω,L=200μH V _{GE} =0V/15V Vclamp=400V See Fig.1, See Fig.2		55		ns
Rise Time	t _r			30		ns
Turn-ON Time	ton			330		ns
Turn-OFF Delay Time	t _d (off)			200		ns
Fall Time	tf			110		ns
Turn-OFF Time	toff			350		ns
Total Gate Charge	Qg	V _{CE} =300V, V _{GE} =15V, I _C =15A		84		nC
Gate to Emitter Charge	Qge			16		nC
Gate to Collector "Miller" Charge	Qgc			37		nC

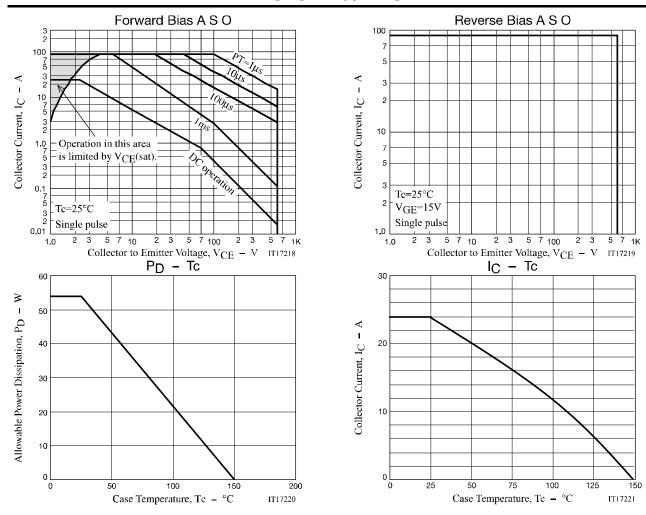
Thermal Characteristics at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Thermal Resistance (junction- Case)	Rth(j-c)	Tc=25°C (our ideal heat dissipation condition)*2	2.33	°C /W
Thermal Resistance (junction- atmosphere)	Rth(j-a)		47.5	°C /W





NGTG12N60TF1G



Package Dimensions

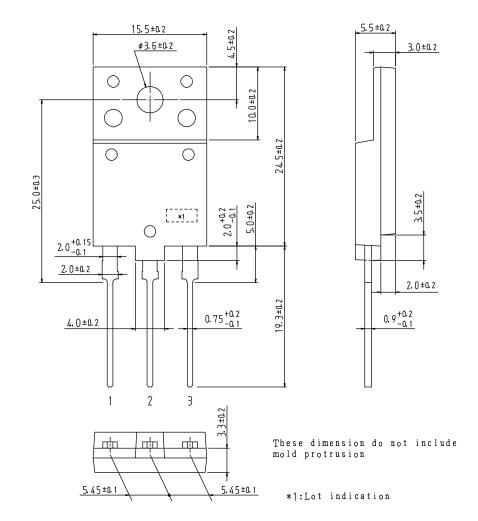
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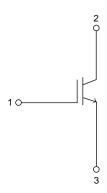
CASE 340AH ISSUE O

Unit: mm

- 1: Gate
- 2: Collector
- 3: Emitter



Electrical Connection



Ordering & Package Information

Device	Package	Shipping	note
NGTG12N60TF1G	TO-3PF-3L SC-94	30 pcs. / tube	Pb-Free

Marking

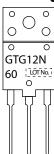


Fig.1 Switching Time Test Circuit

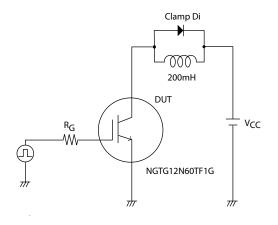
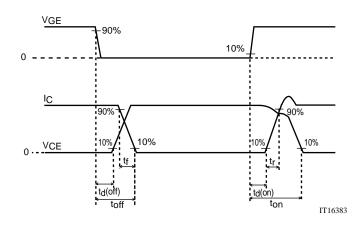


Fig.2 Timing Chart



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